

**EAST - [10604190b.wsp:1]**

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☐ L5: (378) spacer1 and field near effect near transistor1 and first near width  
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spacer1 and compressive near stress and tensile near stress

	<input type="checkbox"/>	<input type="checkbox"/>	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050121745 A1	20050609	11	Method of improving the top plate electrode stress inducing voids for 1T-1R1M process	257/532	438/636	
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050118770 A1	20050602		Method for introducing hydrogen into a channel region of a metal oxide semiconductor (MOS) device	438/305	438/38; 438/958	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050116360 A1	20050602		Complementary field-effect transistors and methods of manufacture		257/900	
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050116294 A1	20050602		Semiconductor device and method for manufacturing the same	257/351	257/353; 257/354	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050112817 A1	20050526	32	Semiconductor device having high drive current and method of manufacture thereof	438/219	257/374	
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050110082 A1	20050526		Semiconductor device having high drive current and method of manufacture thereof	257/341		
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050110043 A1	20050526		Nitride semiconductor substrate, method of fabrication thereof, and semiconductor element	257/194		
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050106898 A1	20050519		Silicon nitride film and semiconductor device, and manufacturing method thereof	438/792		
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050106810 A1	20050519		Stress assisted current driven switching for magnetic memory applications	438/257		
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050106799 A1	20050519		STRESSED SEMICONDUCTOR DEVICE STRUCTURES HAVING GRANULAR SEMICONDUCTOR MATERIAL	438/199		
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20050104922 A1	20050519		Inkjet printhead with integral nozzle plate	347/20		